

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-11. **(canceled)**

Claim 12. **(currently amended)** A fabrication method for the ~~[[FED]]~~ Field Emission Display (FED) cathode plate with an internal via, comprising the steps:

forming and defining a plurality of cathode conductors and a tape line on a substrate at the same time;

depositing a resistive layer to cover the cathode conductors;

sequentially forming a dielectric layer and a gate line on the resistive layer and the tape line;

~~depositing an FED cathode structure from bottom to top including a substrate, a resistive layer, a dielectric layer, and a gate line;~~

~~etching the cathode structure gate line and the dielectric layer to form a cathode plate with the hole and a cavity of [[a]] microtip, a hole upon the cavity of microtip, an internal via, and a contact [[,]] wherein the hole is about 1.6 μ m wide;~~

sloping the plate to a predetermined angle to form a metal layer on the gate line and the internal via to contact with the tape line by evaporation, wherein the predetermined angle is ranged between 10 to 30 degrees;

~~forming a microtip within the microtip cavity by vertical layer evaporation ,including the connection of the internal via and the microtip concurrently completed ; and~~

~~lifting off the excessive deposition on the surface of the plate by immersing the plate in a chemical solution.~~

Claim 13. **(original)** The fabrication method of Claim 12, wherein glass is used to form the substrate.

Claim 14. **(currently amended)** The fabrication method of Claim 12, wherein ~~[[the]]~~ doped silicon is used to form the resistive layer.

Claim 15. **(original)** The fabrication method of Claim 12, wherein niobium-including metal is used to form the cathode conductor, the gate line, and the metal layer.

Claim 16. **(original)** The fabrication method of Claim 12, wherein chromium-including metal is used to form the tape line.

Claim 17. **(original)** The fabrication method of Claim 12, wherein SiO₂ is used to form the dielectric layer.

Claim 18. **(original)** The fabrication method of Claim 12, wherein molybdenum-including metal is used to form the microtip.

Claim 19. **(original)** The fabrication method of Claim 12, further comprising the step of joining and sealing the completed cathode plate to an anode with an adhesive.

Claim 20. **(currently amended)** The fabrication method of Claim ~~[[22]]~~ 19, wherein the adhesive is glass frit.

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Claim 21. **(new)** The fabrication method of Claim 12, wherein the hole is about 1.6 μm wide.